

Dedicated to the memory of Prof. M. Sheinkman effect of ultrasonic treatment on the defect structure of the Si-SiO₂ system

Kropman, Daniel: Dolgov, Sergei; Onufrijevs, Pavels; Dauksta, Edvins Gettering and Defect Engineering in Semiconductor Technology XV 2014 / p. 352-357 : ill <https://doi.org/10.4028/www.scientific.net/SSP.205-206.352> Conference proceedings at Scopus Article at Scopus Conference proceedings at WOS Article at WOS

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Kropman, Daniel: Seeman, Viktor; Dolgov, Sergei; Medvids, Arturs Physica Status Solidi (C) Current Topics in Solid State Physics 2016 / p. 793 - 797 <https://doi.org/10.1002/pssc.201600052> Journal metrics at Scopus Article at Scopus Article at WOS

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel: Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

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Kropman, Daniel: Kärner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, C. A. The 9th International Conference on Global Research and Education : August 9-12, 2010, Riga : digest 2010 / p. 231-233 <https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>

Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties

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